# **Bipolar Power Transistors**

## **NPN Silicon**

#### **Features**

- SOT-223 Surface Mount Packaging
- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	30	Vdc
Collector - Base Voltage	V <sub>CB</sub>	45	Vdc
Emitter - Base Voltage	V <sub>EB</sub>	± 6.0	Vdc
Base Current - Continuous	Ι <sub>Β</sub>	1.0	Adc
Collector Current - Continuous	Ic	3.0	Adc
Collector Current - Peak	I <sub>CM</sub>	5.0	Adc
Total Power Dissipation @ $T_C$ = 25°C Derate above 25°C Total $P_D$ @ $T_A$ = 25°C mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material Total $P_D$ @ $T_A$ = 25°C mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	P <sub>D</sub>	3.0 24 1.7	W mW/°C W
Operating and Storage Junction Temperature Range	$T_{J_i}T_{stg}$	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	42	°C/W
Thermal Resistance, Junction-to-Ambient on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material	$R_{\theta JA}$	75	°C/W
Thermal Resistance, Junction-to-Ambient on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	$R_{\theta JA}$	165	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T <sub>L</sub>	260	°C

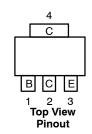


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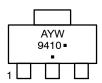
POWER BJT  $I_C = 3.0$  AMPERES  $BV_{CEO} = 30$  VOLTS  $V_{CE(sat)} = 0.2$  VOLTS







SOT-223 CASE 318E STYLE 1



MARKING DIAGRAM

A = Assembly Location

Y = Year

W = Work Week

9410 = Device Code

= Pb-Free Package
(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMJT9410G	SOT-223 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1		1	l	l
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0 Adc)	V <sub>CEO(sus)</sub>	30	-	_	Vdc
Emitter–Base Voltage (I <sub>E</sub> = 50 μAdc, I <sub>C</sub> = 0 Adc)	V <sub>EBO</sub>	6.0	-	-	Vdc
Collector Cutoff Current $(V_{CE} = 25 \text{ Vdc}, R_{BE} = 200 \Omega)$ $(V_{CE} = 25 \text{ Vdc}, R_{BE} = 200 \Omega, T_J = 125^{\circ}\text{C})$	ICER	- -	- -	20 200	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc)	I <sub>EBO</sub>	-	-	10	μAdc
ON CHARACTERISTICS (Note 1)			•		
Collector–Emitter Saturation Voltage ( $I_C = 0.8$ Adc, $I_B = 20$ mAdc) ( $I_C = 1.2$ Adc, $I_B = 20$ mAdc) ( $I_C = 3.0$ Adc, $I_B = 0.3$ Adc)	V <sub>CE(sat)</sub>	- - -	0.105 0.150 -	0.150 0.200 0.450	Vdc
Base-Emitter Saturation Voltage (I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 0.3 Adc)	V <sub>BE(sat)</sub>	-	-	1.25	Vdc
Base–Emitter On Voltage ( $I_C = 1.2 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	_	-	1.10	Vdc
DC Current Gain $ \begin{aligned} &(I_C=0.8 \text{ Adc, V}_{CE}=1.0 \text{ Vdc}) \\ &(I_C=1.2 \text{ Adc, V}_{CE}=1.0 \text{ Vdc}) \\ &(I_C=3.0 \text{ Adc, V}_{CE}=1.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	85 80 60	200 _ _	- - -	-
DYNAMIC CHARACTERISTICS	•				
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0 Adc, f = 1.0 MHz)	C <sub>ob</sub>	-	85	135	pF
Input Capacitance (V <sub>EB</sub> = 8.0 Vdc)	C <sub>ib</sub>	-	200	_	pF
Current–Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 10 Vdc, F <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	-	72	-	MHz

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%. 2.  $f_T = |h_{FE}| \bullet f_{test}$ 

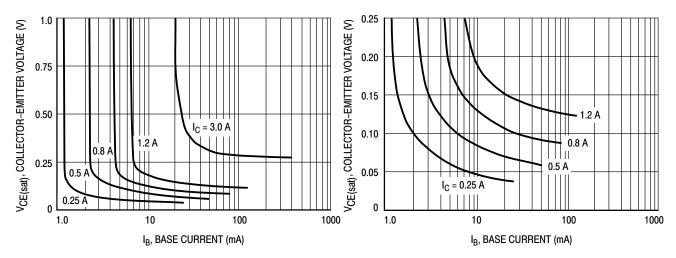


Figure 1. Collector Saturation Region

Figure 2. Collector Saturation Region

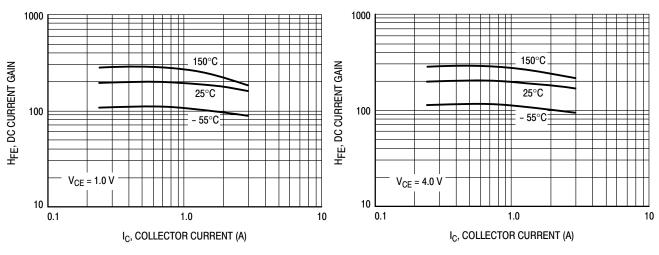


Figure 3. DC Current Gain

Figure 4. DC Current Gain

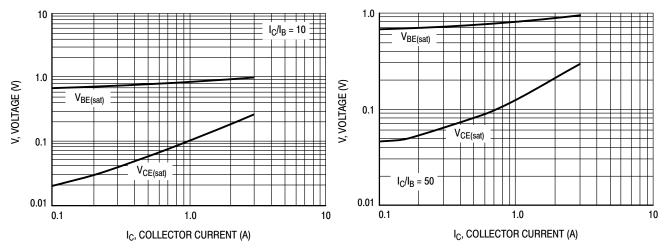


Figure 5. "On" Voltages

Figure 6. "On" Voltages

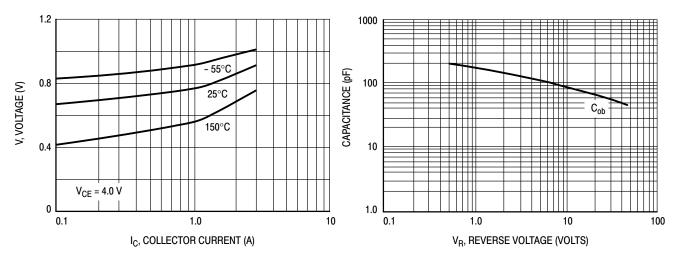


Figure 7.  $V_{BE(on)}$  Voltage

Figure 8. Capacitance

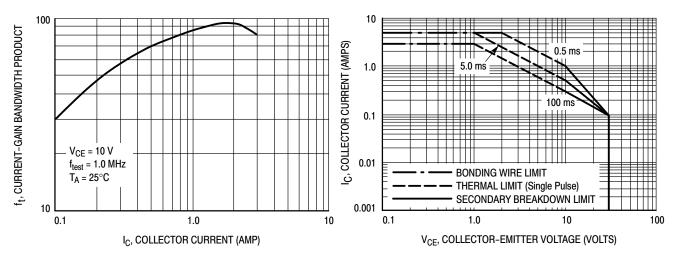


Figure 9. Current-Gain Bandwidth Product

Figure 10. Active Region Safe Operating Area

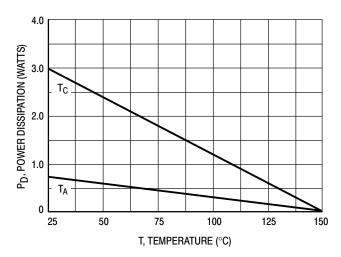


Figure 11. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. Secondary breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 12. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

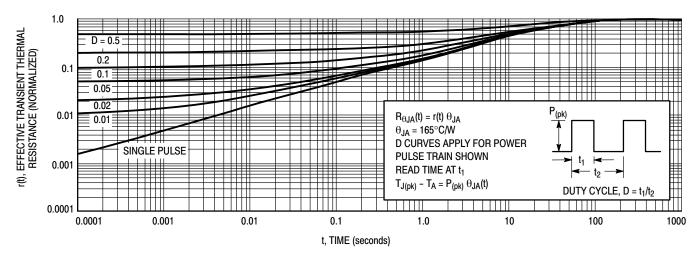


Figure 12. Thermal Response

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